

# SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

# **CPH3455** — General-Purpose Switching Device Applications

### **Features**

- ON-resistance RDS(on)1=80m $\Omega$ (typ.)
- · 4V drive
- · Halogen free compliance

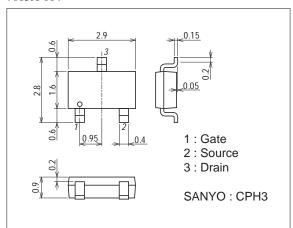
#### **Specifications**

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		35	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID		3	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	12	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm <sup>2</sup> x0.8mm)	1	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### **Package Dimensions**

unit : mm (typ) 7015A-004



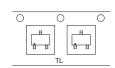
#### **Product & Package Information**

• Package : CPH3

• JEITA, JEDEC : SC-59, TO-236, SOT-23

• Minimum Packing Quantity : 3,000 pcs./reel

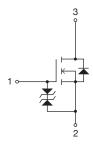
#### Packing Type: TL



## Marking



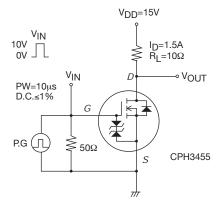
#### **Electrical Connection**

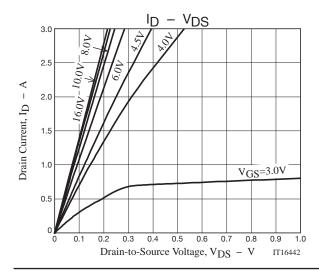


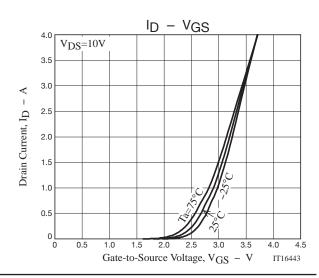
#### Electrical Characteristics at Ta=25°C

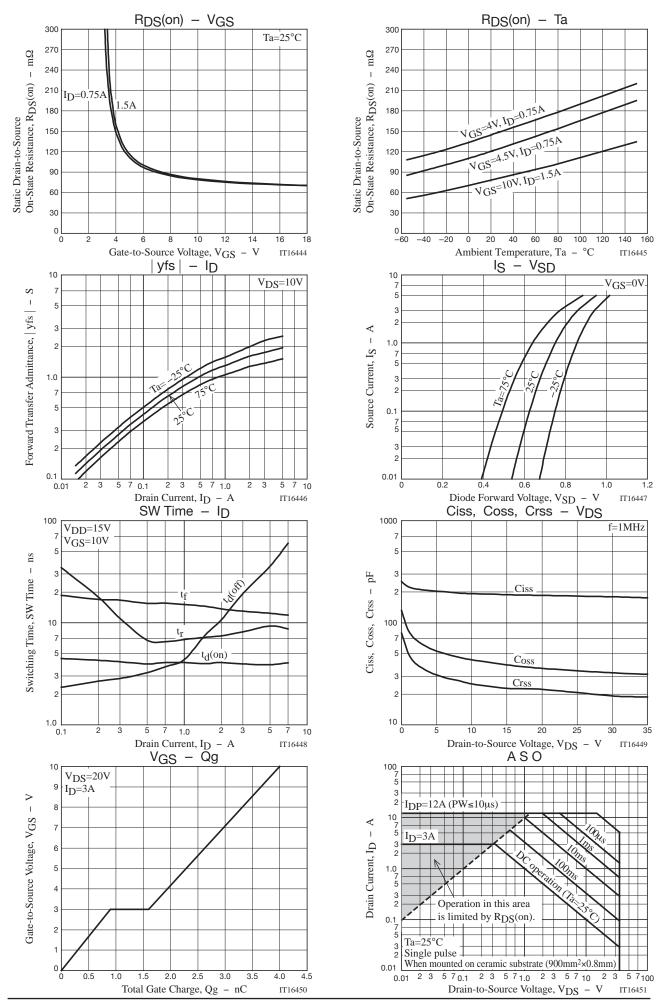
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	35			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =35V, V <sub>GS</sub> =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ
Cutoff Voltage	V <sub>GS</sub> (off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.2		2.6	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =1.5A		1.7		S
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =1.5A, V <sub>G</sub> S=10V		80	104	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =0.75A, V <sub>G</sub> S=4.5V		123	173	mΩ
	R <sub>DS</sub> (on)3	I <sub>D</sub> =0.75A, V <sub>G</sub> S=4V		148	208	mΩ
Input Capacitance	Ciss	V <sub>DS</sub> =20V, f=1MHz		186		pF
Output Capacitance	Coss	V <sub>DS</sub> =20V, f=1MHz		36		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =20V, f=1MHz		22		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit.		4.2		ns
Rise Time	tr	See specified Test Circuit.		4.7		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		15		ns
Fall Time	tf	See specified Test Circuit.		5.7		ns
Total Gate Charge	Qg	V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>D</sub> =3A		4		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>D</sub> =3A		0.9		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>D</sub> =3A		0.7		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =3A, V <sub>GS</sub> =0V		0.86	1.2	V

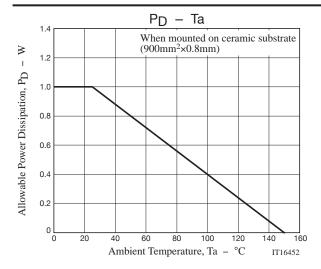
# **Switching Time Test Circuit**











Note on usage: Since the CPH3455 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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